

YJ Planar Schottky Barrier Diode Die Specification

40V 0.2A,13mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB013L040AG-155A

Main Products Characteristics

- Average forward current: $I_F(AV) = 0.2\text{ A}$
- Maximum operating junction temperature: $T_j = 125\text{ }^{\circ}\text{C}$
- ESD rating: >2KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: AL/3.915um

Maximum Ratings

Static Electrical Characteristics (Ta = 25°C)

$I_F = 20\text{mA}/200\text{mA}$
Pulse Test: $t_p = 800\text{ }\mu\text{s}$, $\delta \leq 2\%$

Device Schematics and Outline Drawing

Die Thickness *
Die Size **
Top Metal Pad
Active Area
Top Metal
Back Metal
Steet width

Important Notice

Specification apply to die only. Actual performance may degor5R4(d) ra2C228(c)-4(o)9(n)28()-snc buar5R.ce